Direct observation of a flat band and a partially filled interlayer band in a Cs/graphene/Cs trilayer

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March 22, 2019

We investigate, using angle-resolved photoemission spectroscopy (ARPES), the electronic structure of graphene sandwiched in between two Cs layers with $2 \times 2$ and $\sqrt{3} \times \sqrt{3}$ structures. ARPES reveals that this trilayer has a flat electron energy dispersion at the Fermi level and a partially occupied alkali metal $s$ band. The joint occurrence of these two features together has proven impossible to achieve so far. Here, we introduce a technique to induce these features by the backfolding of graphene bands in a $2 \times 2$ superstructure and
their subsequent hybridization with Cs derived states. The large band renormalization reduces the $\pi$ to $\pi^*$ transition energy at the $M$ point to only 4.15 eV. Hence the excitations of this system can be probed by optical methods with ultraviolet (UV) excitation energy. Performing UV, ultra-high vacuum Raman spectroscopy of this trilayer, we find the Raman $G$ band of graphene is shifted down in frequency by almost 60 cm$^{-1}$ and sharply reduces its Fano asymmetry as the Fermi level is pushed beyond the Lifshitz transition.

**Introduction**

A flat electronic band located energetically at the Fermi level ($E_F$) of a material is an intriguing electronic system [1, 2]. Due to the singularity in the density of states (DOS), the material is unstable against opening of a gap in the electronic structure, that reduces the total energy. This can drive a phase transition of the system into a gapped superconductor or, charge-density wave state, or magnetic ordering. It is a current challenge in materials science to engineer materials with flat bands at $E_F$. Theory suggests that flat bands occur in the dice lattice [3], the Kagome lattice [4, 5, 6], the Lieb lattice [7] and the Tasaki lattice [8]. Some of these flat band systems have recently been experimentally realized, e.g. the Lieb lattice [9, 10]. Graphene related systems also provide ample opportunity for engineering flat bands. Theoretically, a carbon Kagome lattice has been predicted [11], and recently, flat bands have been found in bilayer graphene [12] $\sim$250 meV below $E_F$ and in boron doped graphene nanoribbons [13] $\sim$1.5 eV below $E_F$. More importantly, flat bands in graphene at $E_F$ have been achieved by engineering the stacking order [14, 15, 16, 17], the twist angle [18, 19] and the doping level [20]. Rhombohedrally stacked trilayer graphene exhibits flat bands and, as a consequence, an antiferromagnetic ground state [1, 14, 15, 16, 17]. Bilayer graphene where the two layers are twisted with respect to each other by a magic angle of $\sim$1.1° exhibits a flat band very close to
The discovery of a Mott insulating and superconducting phase in this flat band material \[19\] highlights the rich physics than can be studied in flat band systems. One drawback of these two systems is that they are fabricated from exfoliated flakes and hence can not be prepared deterministically and in large areas. Chemical doping by (earth) alkali(ne) metals has been applied to shift the chemical potential of graphene close to 5/8 filling \[20\] (note: neutral graphene is 1/2 filled). For this filling factor, the Fermi surface contour connects the \(M\) points in the Brillouin zone and a flat band appears at \(E_F\). Flat bands in graphene are closely linked to chiral superconductivity \[21,22\] and conventional superconductivity because the high DOS at the Fermi level enhances \(T_c\). However, for observing conventional superconductivity in alkali metal doped graphene and graphite, just a high density of states is insufficient \[23,24\]. The second condition that is needed to achieve superconductivity is a partially occupied alkali metal band (or: interlayer state) \[23,24\]. These two conditions apparently contradict each other - a high doping level (i.e. a flat band) would mean that all alkali atoms are fully ionized and thus the alkali derived band would be unoccupied whereas a low doping level would allow for the observation of the interlayer state but not the flat band. Alas, all previous works failed to engineer and characterize high-quality systems that allow for simultaneous observation of a flat band and the interlayer state. For example, Ref. \[20\] reports a flat band but no interlayer state and Refs. \[25\] and \[26\] find the interlayer state in bilayer graphene but their doping level is considerably lower than what is needed to occupy the flat band. Notably, in the work by McJesney et al. \[20\], the existence of the partially occupied dopant states could not be clarified because the dopant atoms (K and Ca) did not form an ordered lattice at high doping levels.

The present work addresses these issues by using two inequivalent Cs layers on top of graphene and underneath graphene (between graphene and the substrate). The high structural quality of our samples is achieved by an in-situ, one-step, high amount Cs doping technique. This allows, for the first time, the observation of doping beyond the Lifshitz transition and
the observation of both, an alkali band and a flat band at the Fermi level \[27, 28, 29, 30, 26, 31\]. While the lower Cs layer acts as a charge reservoir layer and is almost fully ionized, the upper Cs layer has partially occupied bands. The Raman spectrum of graphene doped beyond the Lifshitz transition has an abrupt change of the Fano asymmetry (FA) which can be explained by the occupation of the \(\pi^*\) band at the \(M\) point singularity. We expect that this new phase has a high relevance for inducing trivial superconductivity \[24, 32, 33\] and chiral superconductivity \[22\] not only in monolayer graphene but all other sp\(^2\) bonded carbon materials which share an identical singularity in the electronic spectrum.

Results

**Angle-resolved photoemission spectroscopy**

Graphene on Ir(111) is prepared according to a previously published recipe \[34, 35\]. Graphene is then exposed to a very large Cs deposition corresponding to approximately 30 Å deposited on the sample with a rate of about 1 Å per 1 min with the sample being at room temperature. In these high Cs flux and sample temperature conditions, Cs both intercalates under graphene and adsorbs onto the graphene layer and excess Cs does not stick to the surface. The resulting low energy electron diffraction (LEED) pattern (Figure 1a) consists of three subpatterns: one is from the hexagonal graphene lattice, the second one from a Cs \(\sqrt{3} \times \sqrt{3}\)-R30° pattern and the third one from a Cs \(2 \times 2\) phase (the relative angle between graphene and Cs lattices here is zero degrees). From previous works that studied Cs interaction with graphene/Ir(111), it is well known that the \(\sqrt{3} \times \sqrt{3}\)-R30° phase is coming from the alkali metal layer in between graphene and the metal substrate while the Cs \(2 \times 2\) phase grows above the graphene \[36, 35\]. Indeed, when less Cs is deposited, we end up with the intercalated \(\sqrt{3} \times \sqrt{3}\)-R30° phase that we described earlier \[35\]. Our graphene layer is thus encapsulated by one \(\sqrt{3} \times \sqrt{3}\)-R30° Cs layer and one \(2 \times 2\) Cs layer. Figure 1b depicts the energy band structure of this sample as
Figure 1: (a) LEED pattern ($E=73$ eV and $T = 13$ K) and (b) ARPES scan ($h\nu = 31$ eV and $T = 17$ K) of Cs $2\times2$/graphene/Cs $\sqrt{3} \times \sqrt{3}$/Ir(111) along the $\Gamma K M$ directions. The region with the flat band is indicated by a red rectangle. The transition energy at the van Hove singularity of 4.15 eV is indicated. The high symmetry points of the original $1\times1$ and the back folded $2\times2$ BZ are denoted in blue and black color, respectively. (c) Zoom-in to the region indicated by a red rectangle in (b) showing the flat band. (d) Energy distribution curves (EDCs) for the flat band (taken at equidistant steps between 2.2 Å$^{-1}$ (lower EDC) and 2.5 Å$^{-1}$ (upper EDC). Individual EDCs are taken at wavevector steps of 0.01Å and EDCs at every 0.05Å are colored red. (e) Fermi surface map with the Brillouin zones of the graphene and the $2 \times 2$ superstructure indicated. This Fermi surface map has been generated from a symmetrized azimuthal map taken in the first Brillouin zone. All measurements are plotted as the sum of $s$ and $p$ polarization. The $\pi^*$ bands of the original $1 \times 1$ and the $2 \times 2$ superstructure, the Cs band and the $\pi^*$ band from close to the $\Gamma$ point ($\pi_\Gamma$) are indicated.
measured by angle-resolved photoemission spectroscopy (ARPES) along the high symmetry
direction of the 2D BZ. We observe a back folding of the electronic bands consistent with a
$2 \times 2$ superstructure. Interestingly, the $\sqrt{3} \times \sqrt{3}$ Cs order under the graphene does not result
in a back folding. The more efficient screening of the Cs ionic potential by the Ir electrons can
explain this occurrence. For Cs atoms on top of graphene, the potential is sufficiently large to
cause formation of the superstructure. The back folding due to intercalation is well known in
the context of graphite intercalation compounds [37] and has recently also been observed for
oxygen intercalated graphene/Ir [38]. Practically, the $2 \times 2$ back folding means that another
BZ with half the original reciprocal lattice vectors emerges that corresponds to the $2\times2$ unit
cell. The set of high symmetry points of the back folded BZ is labelled as $\Gamma',K'$ and $M'$ (see
Figure 1b and 1e). Due to the back folding, the new $K'$ and $K'^*$ points of the back folded BZ
appear exactly half-way in between $\Gamma K$ and $\Gamma K^*$ of the original BZ. Inspecting the ARPES,
we see that the $\pi$ conduction bands in the $\Gamma'K'^*$ segment have a negative curvature and their
energy maximum is below $E_F$ (at $\sim0.5\text{Å}^{-1}$). However, the $\pi$ conduction bands in the $K'^*M'$
segment have a positive curvature and cross $E_F$ (at $\sim1.1\text{Å}^{-1}$). Since the branch in the $\Gamma'K'^*$
segment is below $E_F$, we have a doping level which is beyond the Lifshitz transition. This
transition is defined by touching of the $\pi$ conduction band maximum at $E_F$ [35]. Note that,
because of the back folding there are two conduction band segments with negative curvature
in the $2 \times 2$ BZ; the one along $\Gamma'K'^*$ and another one along $KM$ (appearing at a wavevector
of $\sim2.2\text{Å}^{-1}$). Back folding of the graphene bands is also key for hybridization with the Cs
bands because in the original $1 \times 1$ cell the Cs bands and the graphene bands are located in
different parts of the BZ. As we will show later in the theory section, this hybridization is key
for inducing a flat band. The fact that the conduction band at the van Hove singularity is below
the Fermi level allows us to determine the transition energy to be $\approx4.15$ eV from ARPES (see
Figure 1b). For optical measurements such as resonance Raman spectroscopy, this value is
expected to be further reduced due to excitonic effects \cite{39, 40}. In the following, we argue that the experimentally observed bandwidth in our doped graphene sample of 4.15 eV is reduced compared to pristine graphene. Pristine graphene on Ir(111) has the $M$ point valence band minimum at an energy of 2.8 eV (see Figure 3b of \cite{41}). The bandwidth between valence band minimum to conduction band maximum at $M$ is more than twice of this value because the conduction bandwidth is larger than the valence band width (see e.g. Figure 3 of \cite{42}). This is explained in a tight-binding picture by a non-zero value of the overlap integral $s$ ($s$ is positive and a typical value is $s \sim 0.1$) \cite{42}. We thus conclude that doping reduces the bandwidth. This means that the Fermi-level shift is non-rigid and that, upon doping the slope of the bands becomes smaller. There are two reasons for the reduction of bandwidth. First, the electron doping causes the lattice to expand \cite{43}. This lattice expansion reduces $\gamma_0$ and hence the transition energy at the $M$ point. Second, the bandwidth is affected by exchange and correlation Coulomb interaction that depend on screening as found by Ulstrup et al. who compared ARPES to density functional theory (DFT) calculations and could explain the bandwidth reduction for doped graphene \cite{44}.

In Figure 1c, we show that the $\pi$ band with negative curvature (red rectangle in Figure 1b) splits in energy near $E_F$; one branch disperses downwards while the other branch forms a flat band located at $E_F$. The energy distribution curves of the flat band are shown in Figure 1d and it is clear that the bandwidth is less than 10 meV. Notably, this bandwidth is even smaller than the one observed for rhombohedral graphene ($\sim 25$ meV) \cite{17}. In Figure 1e, we plot the Fermi surface map and highlight the $2\times 2$ back folding and the alkali metal derived energy bands. Integration of the the states up to the Fermi surface yields a carrier concentration of $n = 5.0 \times 10^{14}$ cm$^{-2}$. Let us compare this to the predicted carrier concentration for 5/8 filling \cite{22}. In the nearest neighbour tight-binding picture the equi-energy contour at 5/8 filling connects adjacent $M$ points in the 2D BZ. For this case, we evaluate a large carrier concentration
Figure 2: (a) Density functional theory calculations (a shift of $-130$ meV was applied to match the experimental Fermi level) of $2 \times 2$ Cs/graphene/$2 \times 2$ Cs along the $\Gamma K M$ directions (high symmetry points of the original $1 \times 1$ BZ) overlaid on the experimental ARPES intensity. The color and the size of the dots indicate the atomic character of the corresponding projected eigenfunction of the Kohn-Sham eigenvalues (white for carbon and cyan for Cs-derived bands). (b) Calculated band structure projected on Iridium (grey), Carbon (black), intercalated Cs (red) and Cs adatoms (blue). The orange lines are calculations of electrostatically doped (i.e. without Cs) free-standing graphene in a $2 \times 2$ supercell. (c) Corresponding partial density of states of C, intercalated Cs and top Cs.

of $n = 9.0 \times 10^{14}$ cm$^{-2}$. The much lower experimentally observed carrier concentration of $n = 5.0 \times 10^{14}$ cm$^{-2}$ is due to trigonal warping effect [45, 37, 42], i.e. the equi-energy contour does not connect adjacent $M$ points by straight lines but rather by curved segments. The curvature of the equi-energy contour is such that the area in between the contour and the BZ boundary is reduced when compared with a straight line equi-energy contour. This reduces the Fermi surface size. Evaluating the carrier concentration of the Cs band, we find 0.54 electrons per $2 \times 2$ unit cell (note: for a full charge transfer, we would have 1 electron). This yields a concentration of $n = 2.56 \times 10^{14}$ cm$^{-2}$. In the following, we will compare the measured band structure with calculated results.

**Calculations of the band structure**

First principles DFT calculations are performed by using a plane-wave pseudopotential approach [46, 47, 48] (see Methods section for details regarding the computational approach and
the modelling of the system). Since the $2 \times 2$ and the $\sqrt{3} \times \sqrt{3}$ Cs superstructures are incommensurate to each other, the real structure is approximated by using $2 \times 2$ Cs adsorbate layers on either side for simplicity. The two Cs layers are relatively shifted within in-plane direction by $a_1 + a_2$, where $a_1$ and $a_2$ are the unit vectors of graphene. After Cs intercalation and subsequent adsorption we find that the graphene-Ir(111) perpendicular distance is 6.17 Å, indicating a complete detaching of graphene from the substate. The deposited Cs atoms are at distances of 2.97 Å (for top Cs) and 3.01 Å (for the bottom Cs) from the graphene layer. These distances are larger than what was obtained for Ba doped graphene in the same reconstruction [49]. As we will show later, this will be important for the position of the interlayer band. The calculated band structure of the Cs $2 \times 2$/graphene/Cs $2 \times 2$/Ir(111) system is plotted in Figure 2a, in the unfolded $1 \times 1$ graphene BZ (note, the bands have been shifted down by 0.13 eV in order to match the experimental Fermi level). The comparison of the calculated results with the experimental ARPES spectrum reveals an impressive agreement between the theoretical and experimental bands which indicates observation of the folded $2 \times 2$ phase induced by Cs adatom reconstruction. The effect of Cs on the band structure is crucial: apart from the obvious doping effect, the Cs $6s$ orbitals forms a hybridization with the carbon derived $2p_z$ orbitals. Along the $KM$ direction, we observe a clear anti-crossing and the opening of a hybridization band gap of $\sim 200$ meV. In the region of the gap opening, the orbital character of the occupied band abruptly changes from C to Cs (see Figures 2 a and c). We also calculated the band structure of electrostatically doped graphene (without Cs) in the back folded BZ (see Figure 2b - orange lines). These show no such gap opening. The anticrossing thus results in an electron-like band with carbon character centered at the $M$ point. The other branch of the band with avoided crossing dispeses along $E_F$ with practically no bandwidth. This produces an extended van Hove singularity with the appearance of a nearly flat band that extends for one half of the $KM$ distance in the 2D BZ which quantitatively explains the origin of the flat band observed in the ARPES.
spectra. Thus the flat band is related not only to the peculiar energy dispersion of graphene at the $M$ point but also to the hybridization with the Cs derived band.

Let us now discuss the role of the two Cs layers which is a key to engineering both the flat band and the partially occupied Cs band for the upper Cs layer. The intercalated Cs layer underneath graphene is almost completely ionized while the upper Cs layer is only partially ionized. Hence the upper Cs layer’s 6s band crosses $E_F$. This is corroborated in the DOS calculation shown in Figure 2c where the partial DOS of the upper Cs layer’s 6s orbital causes the peak at $E_F$.

Interestingly, both the position and the dispersion of this flat band are affected by the spin-orbit coupling induced by the Ir substrate. Although spin-orbit coupling in graphene is negligible, the presence of the Ir substrate induces a relevant reconstruction of the band structure around the $\Gamma$-point. The calculated band structure without the inclusion of the spin-orbit interaction shows that the Ir-derived hole-pocket at the $\Gamma$-point overlaps with graphene $\pi$ bands and are strongly hybridized with them. In particular, we reveal the presence of a flat $p_z$ state just below the Fermi energy at the $M$-point. When we switch on the spin-orbit interaction in the calculation, we get a significant change for the Ir states. In particular, at the $M$ point, spin-orbit coupling induces a gap-opening: the Ir bands become lower in energy by strongly reducing the hybridization with graphene bands. Thus the Ir band becomes fully occupied with a band maximum at 175 meV below $E_F$. This parabolic band shows a Rashba type splitting of 0.079 Å$^{-1}$ which is in agreement with that reported in Ref. [50]. This value can be estimated by the energy position of the surface state of Ir(111)[51].

**Electron phonon coupling**

Let us now turn to the analysis of electron phonon coupling (EPC) which has been observed as a kink in the measured spectral functions close to the Fermi wave vectors along $\Gamma K$ [28, 29, 30]. In Figure 3a, we show ARPES taken in the vicinity of the EPC induced “kink” feature. The self-
Figure 3: Analysis of the ARPES data in the region close to the Fermi level along ΓK′ direction. ARPES was taken at $h\nu = 31$ eV and at $T = 10$ K. (a) ARPES scan in the vicinity of the Fermi wavevector and Fermi energy. The red crosses denote the ARPES maxima and the black line the bare band. (b) and (c) show the real and imaginary part of the self-energy, respectively. (d) the calculated Eliashberg function.

Energy analysis of the kink is performed according to previously established techniques [28, 29, 30]. Figure 3b and 3c depict the real and imaginary part of the self energy, respectively. The corresponding Eliashberg function is shown in Figure 3d and has peaks at $\sim 200$ meV and $\sim 150$ meV for intra- and intervalley EPC, respectively. From integration over the complete Eliashberg function, we extract an EPC constant of $\lambda = 2 \int a^2 F(\omega) d\omega = 0.259$ along ΓK which is the largest $\lambda$ in that crystallographic direction reported in doped graphene so far [28, 29, 30]. The Eliashberg function allows for discriminating the phonon origin of $\lambda$ by restricting the integration to a certain energy range. That is, if we integrate only over the high-energy peak that is due to the Γ point phonon (identical to the Raman G band) we obtain $\lambda_G = 0.203$. Typically, the EPC in KM directions is larger that that of EPC along the ΓK direction by a factor 2-3, see e.g. Refs. [28, 29, 30]. Thus we do expect also a record value of $\lambda$ along the KM direction but unfortunately the flat band in that direction does not allow for extraction of $\lambda$.
because the energy maximum of this band is located at the phonon energy (see Figure 1c where the maximum appears at 2.05 Å⁻¹ with 0.2 eV binding energy). Note that the large λ in the ΓK direction is also nicely in-line with the large Raman downshift of the G Raman mode as shown in the next section.

**Ultra-high vacuum Raman spectroscopy**

We have also performed Raman spectroscopy of graphene doped beyond the Lifshitz transition. Because of the high sensitivity of Cs doped graphene towards air and moisture these experiments are carried out in a homebuilt ultra-high vacuum (UHV) Raman system [35]. The Raman G band position and the FA of the G band depend sensitively on the doping concentration. In our previous work, we have shown that the G band of Cs-doped graphene at the Lifshitz transition assumes an unusually strong Fano lineshape towards high wavenumbers which we explained by electronic Raman scattering [35]. The doping levels in the present work at $5.0 \times 10^{14}$ cm⁻² are clearly beyond the Lifshitz transition [35]. Figure 4a depicts the Raman spectrum for the present experimentally observed band structure along with Raman spectra of pristine graphene and graphene doped at the Lifshitz transition ($n = 4.4 \times 10^{14}$ cm⁻²) from our previous work [35]. It can be seen that for graphene doped beyond the Lifshitz transition, the peak position shifts to lower wavenumbers than was observed previously [52, 53, 35]. This can be understood well in terms of the existing theory describing the doping dependence of phonon modes in terms of lattice expansion and phonon self energy renormalization [43]. Using the relation between carrier concentration and G band frequency that we have developed (figure 6a of Ref. [35]) to describe experiments of doped graphene on Ir(111), we correlate the peak position of the G band phonon mode to a carrier concentration. For the experimentally observed $\omega_G = 1534$ cm⁻¹ we would expect a carrier concentration of $4.6 \times 10^{14}$ cm⁻² in good agreement to the ARPES derived carrier density of $5.0 \times 10^{14}$ cm⁻². Interestingly, for the carrier concentration beyond the Lifshitz transition, the Raman spectrum has a smaller FA. We have performed calculations of
Figure 4: (a) Ultra-high vacuum Raman spectra of graphene/Ir(111) with increasing carrier density (from bottom to top): pristine graphene on Ir(111), Cs doped graphene/Ir(111) at the Lifshitz transition \( n = 4.4 \times 10^{14} \text{ cm}^{-2} \) and Cs 2×2/graphene/Cs \( \sqrt{3} \times \sqrt{3}/\text{Ir(111)} \) \( n = 5.0 \times 10^{14} \text{ cm}^{-2} \). Raman spectra are taken at T=5 K with a UV laser (325 nm) in a vacuum better than \( 1.0 \times 10^{-10} \text{ mbar} \). Note that the first two carrier concentrations are taken from Ref. [35]. (b) Calculations of the Raman spectra for these carrier concentrations across the Lifshitz transition. (c) Value of the asymmetry parameter \( 1/q \) for several carrier concentrations across the Lifshitz transition. (d) and (e) sketches that depict the Raman interference between vibrational \( (G, \text{blue}) \) and electronic Raman scattering (ERS, red) before and beyond the Lifshitz transition.
the Raman spectrum according to previously developed models \[54, 35\] which incorporate the role of electronic Raman scattering (ERS). The calculated Raman spectra (with the electronic structure fitted by TB to the experiment) are shown in Figure 4b and we get a good agreement to the experiment. Figure 4c depicts the FA parameter versus charge carrier concentration, indicating an abrupt decrease to a value close to zero for carrier concentrations beyond the Lifshitz transition. The large FA in Raman for \( E_F \) above the \( M \) point conduction band maximum is a result of the interference of the \( G \) band and ERS that are resonant with the van Hove singularity of density of states (Figure 4d). Increasing the doping level hampers this resonant transition due to Pauli blocking (Fig. 4e) and as a result, the ERS intensity as well as the FA factor decrease. The observed sudden change in \( 1/q \) can therefore be explained by the filling of the states at the \( M \) point van Hove singularity as shown in the ARPES section. Thus the combined information of position and asymmetry from the Raman can be used as a reference for the Raman fingerprinting of the Lifshitz transition.

### Conclusions and outlook

We have prepared trilayer structure with graphene sandwiched in between two Cs layers. The high structural quality of this trilayer allowed the simultaneous observation of the flat \( \pi^* \) and the partially occupied Cs 6s (originating from the top Cs layer) bands. Calculations are in quantitative agreement and reveal strong hybridization of the Cs 6s and the C 2pz orbitals. This hybridization causes a splitting of the \( \pi \) bands into two branches and the formation of an energy gap. One branch disperses flat along \( E_F \) while the other branch disperses to higher binding energies. The present work introduces and applies the idea of using back folding of the graphene bands and subsequent hybridization to alkali metal bands to induce flat bands. The joint observation of both, a flat band and a partially occupied alkali metal band is expected to be highly relevant for future experiments probing superconductivity in Cs/graphene/Cs trilayers.
This is because electrons in the Cs band can couple efficiently to lattice vibrations of graphene. The achieved carrier concentrations lie beyond the realm of liquid ion gating and thus chemical doping provides a real opportunity to engineer SC states in other 2D materials. Our work also guides the synthesis and identification of the Lifshitz phase by Raman spectroscopy. We show that, just at the Lifshitz transition (before $E_F$ moves across the conduction band maximum at the $M$ point) the $G$ band has a maximum FA and then decreases with further increasing $E_F$. Before and at the Lifshitz transition, it is still possible to excite carriers at the $M$ point with UV light. In this phase, the Raman light and hot electron luminescence from the $M$ point conduction band can interfere with each other and produce a strong Fano lineshape. However, if graphene is doped beyond the Lifshitz transition, $E_F$ shifts above the conduction band maximum at the $M$ point and therefore this interference is no more possible and the FA is suppressed. Due to the higher doping, the frequency of the $G$ band decreases even further. This characteristic sequence of FA increase and decrease and the $G$ band frequency downshift is a fingerprint for moving across the Lifshitz transition and will therefore be most useful for probing the Lifshitz regime in transport experiments where ARPES is not possible. Another interesting issue for future study is the effect of the presence of the partially occupied interlayer band to chiral superconductivity \cite{21, 22}. Note that chiral superconductivity was predicted to occur in doped graphene with the flat band at $E_F$ but the effect of an additional allkali metal band has not been studied. Finally, we note that the flat band is common to all sp$^2$ bonded carbon materials. Our approach can therefore be used to induce a flat band at $E_F$ in carbon nanotubes and planar, sp$^2$ bonded organic molecules.
Methods

Angle-resolved photoemission spectroscopy and ultra-high vacuum Raman spectroscopy

ARPES was performed at the BaDEIPh beamline [55] of the Elettra synchrotron in Trieste (Italy) with linear $s$- and $p$- polarisation at $h\nu = 31$ eV. The graphene/Ir(111) samples were prepared in-situ and measured in a vacuum better than $5 \times 10^{-11}$ mbar. Immediately after the synthesis, Cs deposition was carried out in one-shot in an ultra-high vacuum (UHV) chamber from SAES getters with the sample at room temperature. The Fermi surface map from Figure 1 has been generated from a symmetrized azimuthal sweep of the first BZ.

UHV Raman measurements were performed with the sample at $T = 5$ K in the back-scattering geometry using a commercial Raman system (Renishaw) integrated in a homebuilt optical chamber [56], where the exciting and Raman scattered light were coupled into the vacuum using a HeNe laser with wavelength of 325 nm. The $20 \times$ UV objective has a focal distance equal to 13 mm and an NA=0.32. The position of the laser on the sample was checked by a camera in the laser path. All spectra have been calibrated in position and intensity to the O$_2$ vibration at 1555 cm$^{-1}$ (see Ref. [57]). The O$_2$ vibration is visible in the spectra due to the laser path outside the UHV. Sample preparation and measurement were done in-situ and the sample was never exposed to air.

Computational details of the DFT calculation and modelling of the system

First-principles Density Functional Theory calculations were performed to describe the Cs doped graphene system on an Ir(111) surface. We used pseudopotentials approximation for the electron-ion interaction and a plane-wave expansion of the Kohn-Sham wavefunctions as implemented in the VASP package [46, 47, 48]. Generalized gradient approximation (GGA) in the Perdew, Burke and Ernzerhof (PBE) formulation has been adopted for the exchange-
correlation potential. A 400 eV cutoff for the plane waves basis set and $14^2 \Gamma$ centered \textbf{k}-point grid with a gaussian smearing of 0.1 eV have been employed. Long range van-der-Waals interaction (important to describe graphene-substrate interactions) have been included by the Grimme’s semiempirical correction (DFT-D2) to the functional[58]. Spin-orbit coupling has been self-consistently taken into account.

We modelled the system using a $2 \times 2$ graphene unit cell on-top of Ir(111) terminated surface. Due to the lattice mismatch between graphene and ideal Ir(111) surface we fixed the in-plane lattice parameter at the graphene equilibrium value (2.47 Å), thus straining the Iridium in-plane lattice constant by $\approx 9 \%$. The out-of-plane distance between two Iridium layers has been fixed to its bulk value, using the Ir bulk lattice constant (3.84 Å). Four Ir layers and 25 Å of vacuum have been used in the calculation adding dipole correction to account for the inequivalent top and bottom surfaces of the slab. We treated Cs doping adding one Cs atom/unit-cell below the graphene layer as intercalant to detach graphene from the substrate and additional Cs atoms on-top of the graphene layer, both in the hollow sites of the carbon hexagons. With this unit cell, we found that the lowest energy configuration for the adsorbed Cs atoms (above and below graphene) is the one with Cs atoms occupying the center of the two inequivalent hexagons of the $2 \times 2$ unit cell. The positions of the carbon and Cs atoms have been relaxed until the forces on the atoms are less than 0.01 eV/Å, while the Ir atoms were fixed to their bulk sites.

**Calculation of the Raman spectrum**

We have performed calculations of the Raman spectrum according to previously developed model [54, 35]. Raman intensity as a function of Raman shift ($\omega_s$) arises from interference effect between the phonon G band and the electronic Raman spectra (ERS) causing the Fano resonance [54, 35]:

$$I(\omega_s) = [A_G(\omega_s) + A_{ERS}(\omega_s)]^2,$$

(1)
where $A_G = \sum \nu A_\nu$, is the $G$ phonon scattering amplitude which consist of zone center ($\Gamma$ point) $\nu = \text{LO}$ and $\text{iTO}$ modes. $A_{\text{ERS}}$ is the ERS scattering amplitude considering only the first order process. To obtain $A_G$ and $A_{\text{ERS}}$, electronic energy bands and wave functions for the electron-photon, electron-phonon and electron-electron interactions have been obtained from tight binding (TB) method considering up to the three nearest neighbors with TB parameters fitted from ARPES measurement (this work) for each of doping level.

**Acknowledgements**

NE, MH and AG acknowledge the ERC-grant no. 648589 'SUPER-2D' and funding from Quantum Matter and Materials as well as CRC1238 project A1. The stay at the Elettra synchrotron for ARPES experiments has been supported by Horizon 2020 EC programme under Grant Agreement No. 730872 (CALIPSOplus). R.S. acknowledges JSPS KAKENHI (No. JP18H01810).

The authors declare that they have no competing financial interests.

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